

January 1999 Revised June 2005

# 74LVT16245 • 74LVTH16245 Low Voltage 16-Bit Transceiver with 3-STATE Outputs

### **General Description**

The LVT16245 and LVTH16245 contain sixteen non-inverting bidirectional buffers with 3-STATE outputs and is intended for bus oriented applications. The device is byte controlled. Each byte has separate control inputs which can be shorted together for full 16-bit operation. The  $T/\overline{R}$  inputs determine the direction of data flow through the device. The  $\overline{OE}$  inputs disable both the A and B ports by placing them in a high impedance state.

The LVTH16245 data inputs include bushold, eliminating the need for external pull-up resistors to hold unused inputs.

These non-inverting transceivers are designed for low-voltage (3.3V)  $V_{CC}$  applications, but with the capability to provide a TTL interface to a 5V environment. The LVT16245 and LVTH16245 are fabricated with an advanced BiCMOS technology to achieve high speed operation similar to 5V ABT while maintaining low power dissipation.

#### **Features**

- Input and output interface capability to systems at 5V V<sub>CC</sub>
- Bushold data inputs eliminate the need for external pull-up resistors to hold unused inputs (74LVTH16245), also available without bushold feature (74LVT16245).
- Live insertion/extraction permitted
- Power Up/Down high impedance provides glitch-free bus loading
- Outputs source/sink -32 mA/+64 mA
- Functionally compatible with the 74 series 16245
- Latch-up performance exceeds 500 mA
- ESD performance:

Human-body model >2000V

Machine model >200V

Charged-device >1000V

■ Also packaged in plastic Fine-Pitch Ball Grid Array (FBGA) (Preliminary)

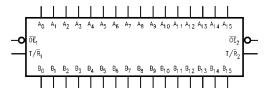
### **Ordering Code:**

Order Number	Package Number	Package Description				
74LVT16245GX (Note 1)	BGA54A (Preliminary)	54-Ball Fine-Pitch Ball Grid Array (FBGA), JEDEC MO-205, 5.5mm Wide [Tape and Reel]				
74LVT16245MEA MS48A (Note 2) 74LVT16245MTD MTD48 (Note 2) 74LVTH16245GX BGA54A (Note 1) (Preliminary)		48-Lead Small Shrink Outline Package (SSOP), JEDEC MO-118, 0.300" Wide				
		48-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 6.1mm Wid				
		54-Ball Fine-Pitch Ball Grid Array (FBGA), JEDEC MO-205, 5.5mm Wide [Tape and Reel]				
74LVTH16245MEA (Note 2)	MS48A	48-Lead Small Shrink Outline Package (SSOP), JEDEC MO-118, 0.300" Wide				
74LVTH16245MTD (Note 2)	MTD48	48-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 6.1mm Wide				

Note 1: BGA package available in Tape and Reel only

Note 2: Devices also available in Tape and Reel. Specify by appending suffix letter "X" to the ordering code.

### **Logic Symbol**

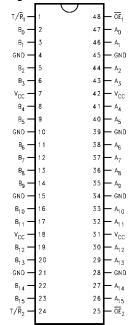


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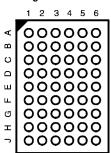
DS500152

# **Connection Diagrams**

Pin Assignment for SSOP and TSSOP



Pin Assignment for FBGA



(Top Thru View)

## **Pin Descriptions**

Pin Names	Description			
<del>OE</del> <sub>n</sub>	Output Enable Input (Active LOW)			
T/R <sub>n</sub>	Transmit/Receive Input			
A <sub>0</sub> -A <sub>15</sub>	Side A Inputs/3-STATE Outputs			
B <sub>0</sub> -B <sub>15</sub>	Side B Inputs/3-STATE Outputs			
NC	No Connect			

# **FBGA Pin Assignments**

	1	2	3	4	5	6
Α	B <sub>0</sub>	NC	T/R <sub>1</sub>	OE <sub>1</sub>	NC	A <sub>0</sub>
В	B <sub>2</sub>	B <sub>1</sub>	NC	NC	A <sub>1</sub>	A <sub>2</sub>
С	B <sub>4</sub>	B <sub>3</sub>	V <sub>CC</sub>	V <sub>CC</sub>	A <sub>3</sub>	A <sub>4</sub>
D	B <sub>6</sub>	B <sub>5</sub>	GND	GND	A <sub>5</sub>	A <sub>6</sub>
E	B <sub>8</sub>	B <sub>7</sub>	GND	GND	A <sub>7</sub>	A <sub>8</sub>
F	B <sub>10</sub>	B <sub>9</sub>	GND	GND	A <sub>9</sub>	A <sub>10</sub>
G	B <sub>12</sub>	B <sub>11</sub>	V <sub>CC</sub>	V <sub>CC</sub>	A <sub>11</sub>	A <sub>12</sub>
Н	B <sub>14</sub>	B <sub>13</sub>	NC	NC	A <sub>13</sub>	A <sub>14</sub>
J	B <sub>15</sub>	NC	T/R <sub>2</sub>	OE <sub>2</sub>	NC	A <sub>15</sub>

## **Truth Tables**

Inp	uts	Outroots.
OE <sub>1</sub>	T/R <sub>1</sub>	Outputs
L L		Bus B <sub>0</sub> -B <sub>7</sub> Data to Bus A <sub>0</sub> -A <sub>7</sub>
L	Н	Bus A <sub>0</sub> -A <sub>7</sub> Data to Bus B <sub>0</sub> -B <sub>7</sub>
Н	Х	HIGH–Z State on A <sub>0</sub> –A <sub>7</sub> ,B <sub>0</sub> –B <sub>7</sub>

Inp	uts	2.1.1.	
OE <sub>2</sub>	T/R <sub>2</sub>	Outputs	
L	L	Bus B <sub>8</sub> -B <sub>15</sub> Data to Bus A <sub>8</sub> -A <sub>15</sub>	
L	Н	Bus A <sub>8</sub> -A <sub>15</sub> Data to Bus B <sub>8</sub> -B <sub>15</sub>	
Н	Х	HIGH–Z State on A <sub>8</sub> –A <sub>15</sub> ,B <sub>8</sub> –B <sub>15</sub>	

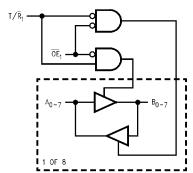
H = HIGH Voltage Level

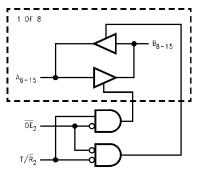
- L = LOW Voltage Level X = Immaterial
- Z = High Impedance

# **Functional Description**

The LVT16245 and LVTH16245 contain sixteen non-inverting bidirectional buffers with 3-STATE outputs. The device is byte controlled with each byte functioning identically, but independent of the other. The control pins can be shorted together to obtain full 16-bit operation.

# **Logic Diagrams**





Note: Please note that these diagrams are provided only for the understanding of logic operations and should not be used to estimate propagation delays.

# Absolute Maximum Ratings(Note 3)

Symbol	Parameter	Value	Conditions	Units
V <sub>CC</sub>	Supply Voltage	-0.5 to +4.6		V
VI	DC Input Voltage	-0.5 to +7.0		V
Vo	Output Voltage	-0.5 to +7.0	Output in 3-STATE	V
		-0.5 to +7.0	Output in HIGH or LOW State (Note 4)	v
I <sub>IK</sub>	DC Input Diode Current	-50	V <sub>I</sub> < GND	mA
I <sub>OK</sub>	DC Output Diode Current	-50	V <sub>O</sub> < GND	mA
Io	DC Output Current	64	Output at HIGH State, V <sub>O</sub> > V <sub>CC</sub>	mA
		128	Output at LOW State, V <sub>O</sub> > V <sub>CC</sub>	IIIA
I <sub>CC</sub>	DC Supply Current per Supply Pin	±64		mA
I <sub>GND</sub>	DC Ground Current per Ground Pin	±128		mA
T <sub>STG</sub>	Storage Temperature Range	-65 to +150		°C

# **Recommended Operating Conditions**

Symbol	Parameter	Min	Max	Units
V <sub>CC</sub>	Supply Voltage	2.7	3.6	V
VI	Input Voltage	0	5.5	V
I <sub>OH</sub>	HIGH-Level Output Current		-32	mA
I <sub>OL</sub>	LOW-Level Output Current		64	mA
T <sub>A</sub>	Free-Air Operating Temperature	-40	+85	°C
Δt/ΔV	Input Edge Rate, V <sub>IN</sub> = 0.8V–2.0V, V <sub>CC</sub> = 3.0V	0	10	ns/V

Note 3: Absolute Maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute maximum rated conditions is not implied.

Note 4: Io Absolute Maximum Ratings must be observed.

### **DC Electrical Characteristics**

Parameter		V <sub>CC</sub>	$T_A = -40^{\circ}C$	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$		Conditions	
raiamete		(V)	Min	Max	Units	Conditions	
Input Clamp Diode Voltage		2.7		-1.2	V	I <sub>I</sub> = -18 mA	
Input HIGH Voltage		2.7-3.6	2.0		V	$V_O \le 0.1V$ or	
Input LOW Voltage	Input LOW Voltage			0.8	V	$V_O \ge V_{CC} - 0.1V$	
Output HIGH Voltage		2.7-3.6	V <sub>CC</sub> - 0.2			I <sub>OH</sub> = -100 μA	
		2.7	2.4		V	I <sub>OH</sub> = -8 mA	
		3.0	2.0			I <sub>OH</sub> = -32 mA	
Output LOW Voltage		2.7		0.2		I <sub>OL</sub> = 100 μA	
		2.7		0.5		I <sub>OL</sub> = 24 mA	
		3.0		0.4	V	I <sub>OL</sub> = 16 mA	
		3.0		0.5		I <sub>OL</sub> = 32 mA	
		3.0		0.55		I <sub>OL</sub> = 64 mA	
Bushold Input Minimum Driv	е	2.0	75		A	V <sub>I</sub> = 0.8V	
		3.0	-75		μΑ	V <sub>I</sub> = 2.0V	
Bushold Input Over-Drive		2.0	500		^	(Note 6)	
Current to Change State		3.0	-500		μА	(Note 7)	
Input Current		3.6		10		V <sub>I</sub> = 5.5V	
	Control Pins	3.6		±1		V <sub>I</sub> = 0V or V <sub>CC</sub>	
	Data Rina	2.6		-5	μА	$V_I = 0V$	
	Data Filis	3.0		1	Ì	$V_I = V_{CC}$	
Power Off Leakage Current		0		±100	μА	$0V \le V_I \text{ or } V_O \le 5.5V$	
Power Up/Down 3-STATE		0.15		±100		V <sub>O</sub> = 0.5V to 3.0V	
Output Current		0-1.5		±100	μΑ	$V_I = GND \text{ or } V_{CC}$	
3-STATE Output Leakage Co	urrent	3.6		-5	μА	V <sub>O</sub> = 0.5V	
3-STATE Output Leakage Co	urrent	3.6		-5	μА	V <sub>O</sub> = 0.0V	
	Input Clamp Diode Voltage Input HIGH Voltage Input LOW Voltage Output HIGH Voltage Output HIGH Voltage  Output LOW Voltage  Bushold Input Minimum Drivi Bushold Input Over-Drive Current to Change State Input Current Power Off Leakage Current Power Up/Down 3-STATE Output Current 3-STATE Output Leakage Current	Input HIGH Voltage Input LOW Voltage Output HIGH Voltage Output HIGH Voltage  Output LOW Voltage  Bushold Input Minimum Drive  Bushold Input Over-Drive Current to Change State Input Current  Control Pins Data Pins  Power Off Leakage Current Power Up/Down 3-STATE	Parameter (V)	Parameter	Parameter	Parameter	

# DC Electrical Characteristics (Continued)

Symbol	Parameter	v <sub>cc</sub>	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$		Units	Conditions	
Cynnbon	T arameter	(V)	Min	Max	Oille	Conditions	
l <sub>OZH</sub>	3-STATE Output Leakage Current	3.6		5	μΑ	V <sub>O</sub> = 3.0V	
I <sub>OZH</sub> (Note 5)	3-STATE Output Leakage Current	3.6		5	μА	V <sub>O</sub> = 3.6V	
I <sub>OZH</sub> +	3-STATE Output Leakage Current	3.6		10	μΑ	$V_{CC} < V_O \le 5.5V$	
I <sub>CCH</sub>	Power Supply Current	3.6		0.19	mA	Outputs HIGH	
I <sub>CCL</sub>	Power Supply Current	3.6		5.0	mA	Outputs LOW	
I <sub>CCZ</sub>	Power Supply Current	3.6		0.19	mA	Outputs Disabled	
I <sub>CCZ+</sub>	Power Supply Current	3.6		0.19	mA	$V_{CC} \le V_O \le 5.5V$ , Outputs Disabled	
$\Delta I_{CC}$	Increase in Power Supply Current	3.6		0.2	mA	One Input at V <sub>CC</sub> – 0.6V	
(Note 8)						Other Inputs at V <sub>CC</sub> or GND	

Note 5: Applies to bushold versions only (74LVTH16245).

Note 6: An external driver must source at least the specified current to switch from LOW-to-HIGH.

Note 7: An external driver must sink at least the specified current to switch from HIGH-to-LOW.

Note 8: This is the increase in supply current for each input that is at the specified voltage level rather than  $V_{CC}$  or GND.

## **Dynamic Switching Characteristics** (Note 9)

Symbol	Parameter	v <sub>cc</sub>	T <sub>A</sub> = 25°C				Conditions	
Symbol	Falametei	(V)	Min Typ		Max	Units	$C_L = 50$ pF, $R_L = 500\Omega$	
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>	3.3		0.8		V	(Note 10)	
V <sub>OLV</sub>	Quiet Output Minimum Dynamic VOL	3.3		-0.8		V	(Note 10)	

Note 9: Characterized in SSOP package. Guaranteed parameter, but not tested.

Note 10: Max number of outputs defined as (n). n-1 data inputs are driven 0V to 3V. Output under test held LOW.

### **AC Electrical Characteristics**

Symbol	Parameter		Units			
Symbol		V <sub>CC</sub> = 3.	3V ± 0.3V	V <sub>CC</sub> = 2.7V		Units
		Min	Max	Min	Max	
t <sub>PLH</sub>	Propagation Delay Data to Output	1.5	3.5	1.5	3.9	ns
t <sub>PHL</sub>		1.3	3.5	1.3	3.9	115
t <sub>PZH</sub>	Output Enable Time	1.5	4.5	1.5	5.3	ns
t <sub>PZL</sub>		1.6	5.3	1.6	6.9	115
t <sub>PHZ</sub>	Output Disable Time	2.3	5.4	2.3	6.1	ns
t <sub>PLZ</sub>		2.2	5.1	2.2	5.4	113
toshl	Output to Output Skew		1.0		1.0	ns
t <sub>OSLH</sub>	(Note 11)		1.0		1.0	110

Note 11: Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t<sub>OSHL</sub>) or LOW-to-HIGH (t<sub>OSLH</sub>). Parameter guaranteed by design.

### Capacitance (Note 12)

Symbol Parameter		Parameter	Conditions	Typical	Units
1	C <sub>IN</sub>	Input Capacitance	$V_{CC} = 0V$ , $V_I = 0V$ or $V_{CC}$	4	pF
	C <sub>I/O</sub>	Input/Output Capacitance	$V_{CC} = 3.0V$ , $V_{O} = 0V$ or $V_{CC}$	8	pF

 $\textbf{Note 12:} \ \, \textbf{Capacitance is measured at frequency } f = 1 \ \, \textbf{MHz}, per \ \, \textbf{MIL-STD-883}, \, \textbf{Method 3012}.$ 

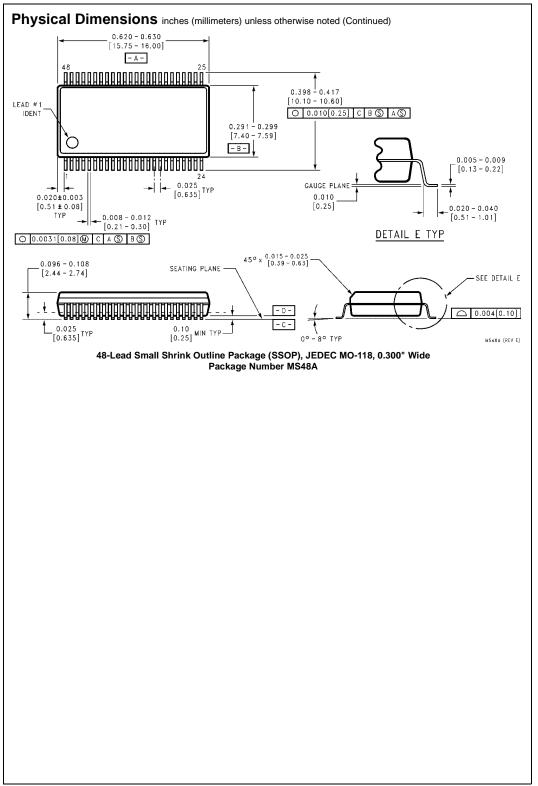
#### 74LVT16245 • 74LVTH16245 Physical Dimensions inches (millimeters) unless otherwise noted ○ 0.10 B В 5.5 8.0 Α (0.8)0.4 0.10 A -(0.75) 000000 ABCDEFGHJ PIN ONE 8 0.8 1/23<sup>j</sup>456 Top **Bottom** 54X 0.5<sup>+0.05</sup> View View 0.15(M) C A B 0.08(M) C // 0.15 C SEATING PLANE 0.45 0.35 1.4MAX ○ 0.10 C

#### NOTES:

- A. THIS PACKAGE CONFORMS TO JEDEC M0-205
- **B. ALL DIMENSIONS IN MILLIMETERS**
- C. LAND PATTERN RECOMMENDATION: NSMD (Non Solder Mask Defined)
  .35MM DIA PADS WITH A SOLDERMASK OPENING OF .45MM CONCENTRIC TO PADS
  D. DRAWING CONFORMS TO ASME Y14.5M-1994

### BGA54ArevD

54-Ball Fine-Pitch Ball Grid Array (FBGA), JEDEC MO-205, 5.5mm Wide Package Number BGA54A Preliminary



### Physical Dimensions inches (millimeters) unless otherwise noted (Continued) 12.50±0.10 0.40 TYP -B-99. 9.20 8.10 50. O.2 C B A ALL LEAD TIPS PIN #1 IDENT 0.50 LAND PATTERN RECOMMENDATION 0.1 C SEE DETAIL A 0.90+0.15 ALL LEAD TIPS 0.09-0.20 0.10±0.05 0.17-0.27 0.50 ♦ 0.13@ A BS CS 12.00' TOP & BOTTOM DIMENSIONS ARE IN MILLIMETERS R0.16 GAGE PLANE 0.25 NOTES: A. CONFORMS TO JEDEC REGISTRATION MO-153, VARIATION ED, DATE 4/97. B. DIMENSIONS ARE IN MILLIMETERS. SEATING PLANE 0.60±0.10 1.00 C. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS. D. DIMENSIONS AND TOLERANCES PER ANSI Y14.5M, 1982. DETAIL A MTD48REVC

48-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 6.1mm Wide Package Number MTD48

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